Manijeh Razeghi

List of Publications by Year
in descending order

347	15,505	15880 67	33145 104
papers	citations	h-index	g-index

355	355	355	8278
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	High Power Mid-Infrared Quantum Cascade Lasers Grown on GaAs. Photonics, 2022, 9, 231.	0.9	8
2	Low Dark Current Deep UV AlGaN Photodetectors on AlN Substrate. IEEE Journal of Quantum Electronics, 2022, 58, 1-5.	1.0	7
3	Resonant cavity enhanced heterojunction phototransistors based on type-II superlattices. Infrared Physics and Technology, 2021, 113, 103552.	1.3	5
4	Multi-band SWIR-MWIR-LWIR Type-II superlattice based infrared photodetector. Results in Optics, 2021, 2, 100054.	0.9	18
5	Study of Phase Transition in MOCVD Grown Ga2O3 from Î² to Î² Phase by Ex Situ and In Situ Annealing. Photonics, 2021, 8, 17.	0.9	18
6	High Power, Widely Tunable, and Beam Steerable Mid-infrared Quantum Cascade Lasers. NATO Science for Peace and Security Series B: Physics and Biophysics, 2021, , 21-34.	0.2	0
7	Highly Conductive Co-Doped Ga2O3:Si-In Grown by MOCVD. Coatings, 2021, 11, 287.	1.2	7
8	Performance analysis of infrared heterojunction phototransistors based on Type-II superlattices. Infrared Physics and Technology, 2021, 113, 103641.	1.3	3
9	Mid-wavelength infrared avalanche photodetector with AlAsSb/GaSb superlattice. Scientific Reports, 2021, 11, 7104.	1.6	16
10	Low Noise Short Wavelength Infrared Avalanche Photodetector Using SB-Based Strained Layer Superlattice. Photonics, 2021, 8, 148.	0.9	3
11	Geiger-Mode Operation of AlGaN Avalanche Photodiodes at 255 nm. IEEE Journal of Quantum Electronics, 2021, 57, 1-6.	1.0	11
12	Harmonic injection locking of high-power mid-infrared quantum cascade lasers. Photonics Research, 2021, 9, 1078.	3.4	8
13	High-brightness LWIR quantum cascade lasers. Optics Letters, 2021, 46, 5193.	1.7	6
14	Band-structure-engineered high-gain LWIR photodetector based on a type-II superlattice. Light: Science and Applications, 2021, 10, 17.	7.7	30
15	Microstrip Array Ring FETs with 2D p-Ga2O3 Channels Grown by MOCVD. Photonics, 2021, 8, 578.	0.9	4
16	InAs/GaSb type II superlattices: A developing material system for third generation of IR imaging. , 2020, , 379-413.		10
17	Demonstration of Planar Type-II Superlattice-Based Photodetectors Using Silicon Ion-Implantation. Photonics, 2020, 7, 68.	0.9	7
18	Room temperature quantum cascade laser with â¼31% wall-plug efficiency. AIP Advances, 2020, 10, .	0.6	17

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19	High performance InAs/InAsSb Type-II superlattice mid-wavelength infrared photodetectors with double barrier. Infrared Physics and Technology, 2020, 109, 103439.	1.3	15
20	Avalanche Photodetector Based on InAs/InSb Superlattice. Quantum Reports, 2020, 2, 591-599.	0.6	15
21	Type-II superlattice-based heterojunction phototransistors for high speed applications. Infrared Physics and Technology, 2020, 108, 103350.	1.3	9
22	Planar nBn type-II superlattice mid-wavelength infrared photodetectors using zinc ion-implantation. Applied Physics Letters, 2020, 116, .	1.5	15
23	Mid-wavelength infrared high operating temperature pBn photodetectors based on type-II InAs/InAsSb superlattice. AIP Advances, 2020, 10, .	0.6	38
24	High performance Zn-diffused planar mid-wavelength infrared type-II InAs/InAs1âˆ’xSbx superlattice photodetector by MOCVD. Applied Physics Letters, 2020, 116, .	1.5	17
25	Continuous wave quantum cascade lasers with 5.6 W output power at room temperature and 41% wall-plug efficiency in cryogenic operation. AIP Advances, 2020, 10, .	0.6	13
26	High-speed short wavelength infrared heterojunction phototransistors based on type II superlattices. , 2020, , .		2
27	Sb-based third generation at Center for Quantum Devices. , 2020, , .		1
28	High power continuous wave operation of single mode quantum cascade lasers up to 5 W spanning Î»â¼3.8-8.3 Âµm. Optics Express, 2020, 28, 15181.	1.7	13
29	Room temperature quantum cascade lasers with 22% wall plug efficiency in continuous-wave operation. Optics Express, 2020, 28, 17532.	1.7	23
30	Demonstration of mid-wavelength infrared nBn photodetectors based on type-II InAs/InAs1-xSbx superlattice grown by metal-organic chemical vapor deposition. Applied Physics Letters, 2019, 115, .	1.5	16
31	MOCVD grown Î²-Ga₂O₃ metal-oxide-semiconductor field effect transistors on sapphire. Applied Physics Express, 2019, 12, 095503.	1.1	19
32	High speed antimony-based superlattice photodetectors transferred on sapphire. Applied Physics Express, 2019, 12, 116502.	1.1	8
33	Surface Emitting, Tunable, Mid-Infrared Laser with High Output Power and Stable Output Beam. Scientific Reports, 2019, 9, 549.	1.6	10
34	Extended short wavelength infrared heterojunction phototransistors based on type II superlattices. Applied Physics Letters, 2019, 114, 191109.	1.5	15
35	Ga₂O₃ metal-oxide-semiconductor field effect transistors on sapphire substrate by MOCVD. Semiconductor Science and Technology, 2019, 34, 08LT01.	1.0	27
36	Room temperature terahertz semiconductor frequency comb. Nature Communications, 2019, 10, 2403.	5.8	50

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37	AlGaN/AlN MOVPE heteroepitaxy: pulsed co-doping SiH₄ and TMIn. Semiconductor Science and Technology, 2019, 34, 075028.	1.0	8
38	Investigation of surface leakage reduction for small pitch shortwave infrared photodetectors. Semiconductor Science and Technology, 2019, 34, 06LT01.	1.0	4
39	Typeâ€“II superlattices base visible/extended shortâ€“wavelength infrared photodetectors with a bandstructureâ€“engineered photoâ€“generated carrier extractor. Scientific Reports, 2019, 9, 5003.	1.6	20
40	Fabrication of 12 Âµm pixel-pitch 1280 Ã— 1024 extended short wavelength infrared focal plane array using heterojunction type-II superlattice-based photodetectors. Semiconductor Science and Technology, 2019, 34, 03LT01.	1.0	12
41	Suppressing Spectral Crosstalk in Dual-Band Long- Wavelength Infrared Photodetectors With Monolithically Integrated Air-Gapped Distributed Bragg Reflectors. IEEE Journal of Quantum Electronics, 2019, 55, 1-6.	1.0	13
42	High quantum efficiency mid-wavelength infrared type-II InAs/InAs1â^'xSbx superlattice photodiodes grown by metal-organic chemical vapor deposition. Applied Physics Letters, 2019, 114, .	1.5	22
43	Strain-Induced Metastable Phase Stabilization in Ga₂O₃ Thin Films. ACS Applied Materials & Interfaces, 2019, 11, 5536-5543.	4.0	42
44	High brightness ultraviolet light-emitting diodes grown on patterned silicon substrate. Materials Science in Semiconductor Processing, 2019, 90, 87-91.	1.9	15
45	Antimonite-based gap-engineered type-II superlattice materials grown by MBE and MOCVD for the third generation of infrared imagers. , 2019, , .		5
46	High-power, continuous-wave, phase-locked quantum cascade laser arrays emitting at 8 Âµm. Optics Express, 2019, 27, 15776.	1.7	36
47	(Invited) MOCVD-Grown Ga₂O₃ Field Effect Transistors on Sapphire. ECS Meeting Abstracts, 2019, MA2019-02, 1356-1356.	0.0	1
48	New design strategies for multifunctional and inexpensive quantum cascade lasers. , 2019, , .		0
49	Room temperature THz frequency comb based on QCL. , 2019, , .		0
50	Thin-Film Antimonide-Based Photodetectors Integrated on Si. IEEE Journal of Quantum Electronics, 2018, 54, 1-7.	1.0	10
51	Shortwave quantum cascade laser frequency comb for multi-heterodyne spectroscopy. Applied Physics Letters, 2018, 112, 141104.	1.5	32
52	Sandwich method to grow high quality AlN by MOCVD. Journal Physics D: Applied Physics, 2018, 51, 085104.	1.3	32
53	Phase-locked, high power, mid-infrared quantum cascade laser arrays. Applied Physics Letters, 2018, 112, .	1.5	18
54	Room temperature operation of InxGa1â^'xSb/InAs type-II quantum well infrared photodetectors grown by MOCVD. Applied Physics Letters, 2018, 112, .	1.5	21

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55	Breaking Spectral and Performance Barriers for Diode Lasers with Material Innovation. , 2018, , .		0
56	Single-mode, high-power, mid-infrared, quantum cascade laser phased arrays. Scientific Reports, 2018, 8, 14866.	1.6	15
57	High Frequency Extended Short-Wavelength Infrared Heterojunction Photodetectors Based on InAs/GaSb/AlSb Type-II Superlattices. IEEE Journal of Quantum Electronics, 2018, 54, 1-5.	1.0	6
58	Demonstration of long wavelength infrared type-II InAs/InAs1-xSbx superlattices photodiodes on GaSb substrate grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2018, 112, .	1.5	20
59	nBn extended short-wavelength infrared focal plane array. Optics Letters, 2018, 43, 591.	1.7	36
60	Type-II InAs/GaSb/AlSb superlattice-based heterojunction phototransistors: back to the future. , 2018, , .		3
61	Review of high power frequency comb sources based on InP: from MIR to THz at CQD. , 2018, , .		2
62	Impact of scaling base thickness on the performance of heterojunction phototransistors. Nanotechnology, 2017, 28, 10LT01.	1.3	21
63	A lifetime of contributions to the world of semiconductors using the Czochralski invention. Vacuum, 2017, 146, 308-328.	1.6	2
64	Backgroundâ€“limited long wavelength infrared InAs/InAs1â^' xSbx type-II superlattice-based photodetectors operating at 110 K. APL Materials, 2017, 5, .	2.2	33
65	High efficiency quantum cascade laser frequency comb. Scientific Reports, 2017, 7, 43806.	1.6	25
66	Extended short-wavelength infrared nBn photodetectors based on type-II InAs/AlSb/GaSb superlattices with an AlAsSb/GaSb superlattice barrier. Applied Physics Letters, 2017, 110, .	1.5	50
67	Recent advances in InAs/InAs_{1-x}Sb_x/AlAs_{1-x}Sb_x gap-engineered type-II superlattice-based photodetectors. Proceedings of SPIE, 2017, , .	0.8	10
68	Dispersion compensated mid-infrared quantum cascade laser frequency comb with high power output. AIP Advances, 2017, 7, .	0.6	15
69	Biasâ€“selectable nBn dualâ€“band longâ€“/very longâ€–wavelength infrared photodetectors based on InAs/InAs1â^'xSbx/AlAs1â^'xSbx typeâ€“II superlattices. Scientific Reports, 2017, 7, 3379.	1.6	60
70	Preface to Special Topic: Emerging materials for photonics. APL Materials, 2017, 5, 035101.	2.2	0
71	Study of Au coated ZnO nanoarrays for surface enhanced Raman scattering chemical sensing. Journal of Materials Chemistry C, 2017, 5, 3528-3535.	2.7	47
72	Dark current reduction in microjunction-based double electron barrier type-II InAs/InAsSb superlattice long-wavelength infrared photodetectors. Scientific Reports, 2017, 7, 12617.	1.6	17

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73	Monolithic beam steering in a mid-infrared, surface-emitting, photonic integrated circuit. Scientific Reports, 2017, 7, 8472.	1.6	8
74	Direct growth of thick AlN layers on nanopatterned Si substrates by cantilever epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600363.	0.8	14
75	Bias-selectable three-color short-, extended-short-, and mid-wavelength infrared photodetectors based on type-II InAs/GaSb/AlSb superlattices. Optics Letters, 2017, 42, 4275.	1.7	13
76	High performance monolithic, broadly tunable mid-infrared quantum cascade lasers. Optica, 2017, 4, 1228.	4.8	28
77	Type-II superlattice-based extended short-wavelength infrared focal plane array with an AlAsSb/GaSb superlattice etch-stop layer to allow near-visible light detection. Optics Letters, 2017, 42, 4299.	1.7	18
78	Recent progress of quantum cascade laser research from 3 to 12â€‰â€‰Î¼m at the Center for Quantum Devices [Invited]. Applied Optics, 2017, 56, H30.	0.9	53
79	Progress in monolithic, broadband, widely tunable midinfrared quantum cascade lasers. Optical Engineering, 2017, 57, 1.	0.5	4
80	Room temperature continuous wave, monolithic tunable THz sources based on highly efficient mid-infrared quantum cascade lasers. Scientific Reports, 2016, 6, 23595.	1.6	86
81	Mid-wavelength infrared heterojunction phototransistors based on type-II InAs/AlSb/GaSb superlattices. Applied Physics Letters, 2016, 109, .	1.5	25
82	Monolithically, widely tunable quantum cascade lasers based on a heterogeneous active region design. Scientific Reports, 2016, 6, 25213.	1.6	38
83	High performance bias-selectable three-color Short-wave/Mid-wave/Long-wave Infrared Photodetectors based on Type-II InAs/GaSb/AlSb superlattices. Scientific Reports, 2016, 6, 24144.	1.6	86
84	High power continuous operation of a widely tunable quantum cascade laser with an integrated amplifier. Applied Physics Letters, 2015, 107, .	1.5	19
85	High-performance short-wavelength infrared photodetectors based on type-II InAs/InAs1-xSbx/AlAs1âˆ’xSbx superlattices. Applied Physics Letters, 2015, 107, 141104.	1.5	39
86	High power frequency comb based on mid-infrared quantum cascade laser at Î»â€‰â¼â€‰9â€‰Î¼m. Applied Physics Letters, 2015, 106, .	1.5	51
87	Bias-selectable dual-band mid-/long-wavelength infrared photodetectors based on InAs/InAs1âˆ’xSbx type-II superlattices. Applied Physics Letters, 2015, 106, .	1.5	75
88	High brightness angled cavity quantum cascade lasers. Applied Physics Letters, 2015, 106, .	1.5	52
89	Quantum cascade lasers: from tool to product. Optics Express, 2015, 23, 8462.	1.7	168
90	Ultra-broadband quantum cascade laser, tunable over 760 cm^âˆ’1, with balanced gain. Optics Express, 2015, 23, 21159.	1.7	42

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91	Superlattice-based quantum devices: from theory to practical applications. Waves in Random and Complex Media, 2014, 24, 240-249.	1.6	0
92	Widely tunable room temperature semiconductor terahertz source. Applied Physics Letters, 2014, 105, .	1.5	67
93	Generation-recombination and trap-assisted tunneling in long wavelength infrared minority electron unipolar photodetectors based on InAs/GaSb superlattice. Applied Physics Letters, 2014, 104, 053508.	1.5	28
94	Continuous operation of a monolithic semiconductor terahertz source at room temperature. Applied Physics Letters, 2014, 104, .	1.5	80
95	Advances in mid-infrared detection and imaging: a key issues review. Reports on Progress in Physics, 2014, 77, 082401.	8.1	114
96	InAs/InAs1â^'xSbx type-II superlattices for high performance long wavelength infrared detection. Applied Physics Letters, 2014, 105, .	1.5	98
97	High Performance Solar-Blind Ultraviolet <inline-formula> <tex-math notation="TeX">(320 imes 256) </tex-math></inline-formula> Focal Plane Arrays Based on Al_{<italic>x</italic>}Ga_{1-<italic>x</italic>}N. IEEE Journal of Quantum Electronics, 2014, 50, 593-597.	1.0	8
98	Measurements of carbon monoxide mixing ratios in Houston using a compact high-power CW DFB-QCL-based QEPAS sensor. Applied Physics B: Lasers and Optics, 2014, 117, 519-526.	1.1	7
99	Antimonide-Based Type II Superlattices: A Superior Candidate for the Third Generation of Infrared Imaging Systems. Journal of Electronic Materials, 2014, 43, 2802-2807.	1.0	30
100	High performance photodiodes based on InAs/InAsSb type-II superlattices for very long wavelength infrared detection. Applied Physics Letters, 2014, 104, .	1.5	64
101	Investigation of impurities in type-II InAs/GaSb superlattices via capacitance-voltage measurement. Applied Physics Letters, 2013, 103, .	1.5	15
102	Surface plasmon enhanced light emission from AlGaN-based ultraviolet light-emitting diodes grown on Si (111). Applied Physics Letters, 2013, 102, 211110.	1.5	72
103	Demonstration of high performance bias-selectable dual-band short-/mid-wavelength infrared photodetectors based on type-II InAs/GaSb/AlSb superlattices. Applied Physics Letters, 2013, 102, 011108.	1.5	51
104	Al_xGa_{1-x}N-based back-illuminated solar-blind photodetectors with external quantum efficiency of 89%. Applied Physics Letters, 2013, 103, 191108.	1.5	143
105	Near milliwatt power AlGaN-based ultraviolet light emitting diodes based on lateral epitaxial overgrowth of AlN on Si(111). Applied Physics Letters, 2013, 102, 011106.	1.5	50
106	Advances in antimonide-based Type-II superlattices for infrared detection and imaging at center for quantum devices. Infrared Physics and Technology, 2013, 59, 41-52.	1.3	57
107	Crack-free AlGaN for solar-blind focal plane arrays through reduced area epitaxy. Applied Physics Letters, 2013, 102, .	1.5	33
108	Room temperature terahertz quantum cascade laser sources with 215â€‰Î¼W output power through epilayer-down mounting. Applied Physics Letters, 2013, 103, 011101.	1.5	45

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109	Al_xGa_{1â^'x}N-based solar-blind ultraviolet photodetector based on lateral epitaxial overgrowth of AlN on Si substrate. Applied Physics Letters, 2013, 103, 181113.	1.5	41
110	Active and passive infrared imager based on short-wave and mid-wave type-II superlattice dual-band detectors. Optics Letters, 2013, 38, 22.	1.7	25
111	Extended electrical tuning of quantum cascade lasers with digital concatenated gratings. Applied Physics Letters, 2013, 103, .	1.5	38
112	High performance terahertz quantum cascade laser sources based on intracavity difference frequency generation. Optics Express, 2013, 21, 968.	1.7	37
113	World's first demonstration of type-II superlattice dual band 640x512 LWIR focal plane array. Proceedings of SPIE, 2012, , .	0.8	12
114	Al_xGa_1â^'xNâ€“based deep-ultraviolet 320Ã—256 focal plane array. Optics Letters, 2012, 37, 896.	1.7	38
115	Widely tuned room temperature terahertz quantum cascade laser sources based on difference-frequency generation. Applied Physics Letters, 2012, 101, .	1.5	56
116	Surface leakage investigation via gated type-II InAs/GaSb long-wavelength infrared photodetectors. Applied Physics Letters, 2012, 101, .	1.5	24
117	High power, continuous wave, room temperature operation of Î»â€‰â^¼â€‰3.4â€‰Î¼m and Î»â€‰â^¼â€‰3.55â€‰Î¼m InP-b cascade lasers. Applied Physics Letters, 2012, 100, .	1.5	67
118	Highly selective two-color mid-wave and long-wave infrared detector hybrid based on Type-II superlattices. Optics Letters, 2012, 37, 4744.	1.7	36
119	Sampled grating, distributed feedback quantum cascade lasers with broad tunability and continuous operation at room temperature. Applied Physics Letters, 2012, 100, .	1.5	67
120	Demonstration of shortwavelength infrared photodiodes based on type-II InAs/GaSb/AlSb superlattices. Applied Physics Letters, 2012, 100, .	1.5	95
121	Room temperature continuous wave operation of Î»â€‰â^¼â€‰3â€“3.2â€‰Î¼m quantum cascade lasers. Applied Physics Letters, 2012, 101, .	1.5	98
122	Thermal Conductivity of InAs/GaSb TypeÂII Superlattice. Journal of Electronic Materials, 2012, 41, 2322-2325.	1.0	8
123	High Operability 1024$,imes,$1024 Long Wavelength Type-II Superlattice Focal Plane Array. IEEE Journal of Quantum Electronics, 2012, 48, 221-228.	1.0	30
124	Stable single mode terahertz semiconductor sources at room temperature. , 2011, , .		0
125	Surface leakage current reduction in long wavelength infrared type-II InAs/GaSb superlattice photodiodes. Applied Physics Letters, 2011, 98, .	1.5	24
126	Elimination of surface leakage in gate controlled type-II InAs/GaSb mid-infrared photodetectors. Applied Physics Letters, 2011, 99, .	1.5	34

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127	High performance dual-band long-wave infrared focal plane array based on type-II InAs/GaSb superlattices. , 2011, , .		0
128	High Operability 1024Ã—1024 Long Wavelength Infrared Focal Plane Array Base on Type-II InAsâˆ•GaSb Superlattice. AIP Conference Proceedings, 2011, , .	0.3	7
129	Room temperature single-mode terahertz sources based on intracavity difference-frequency generation in quantum cascade lasers. Applied Physics Letters, 2011, 99, .	1.5	82
130	Room temperature quantum cascade lasers with 27% wall plug efficiency. Applied Physics Letters, 2011, 98, .	1.5	289
131	2.4 W room temperature continuous wave operation of distributed feedback quantum cascade lasers. Applied Physics Letters, 2011, 98, .	1.5	103
132	High operating temperature midwave infrared photodiodes and focal plane arrays based on type-II InAs/GaSb superlattices. Applied Physics Letters, 2011, 98, 143501.	1.5	102
133	Type-II superlattice dual-band LWIR imager with M-barrier and Fabryâ€“Perot resonance. Optics Letters, 2011, 36, 2560.	1.7	38
134	Growth and Characterization of Long-Wavelength Infrared Type-II Superlattice Photodiodes on a 3-in GaSb Wafer. IEEE Journal of Quantum Electronics, 2011, 47, 686-690.	1.0	61
135	Type-II InAs/GaSb photodiodes and focal plane arrays aimed at high operating temperatures. Opto-electronics Review, 2011, 19, .	2.4	35
136	Recent advances in IR semiconductor laser diodes and future trends. , 2011, , .		0
137	High power, continuous wave, quantum cascade ring laser. Applied Physics Letters, 2011, 99, .	1.5	51
138	Deep ultraviolet (254 nm) focal plane array. Proceedings of SPIE, 2011, , .	0.8	4
139	Widely tunable single-mode high power quantum cascade lasers. , 2011, , .		7
140	High performance long wavelength infrared mega-pixel focal plane array based on type-II superlattices. Applied Physics Letters, 2010, 97, .	1.5	70
141	Technology of Quantum Devices. , 2010, , .		59
142	Photovoltaic MWIR Type-II Superlattice Focal Plane Array on GaAs Substrate. IEEE Journal of Quantum Electronics, 2010, 46, 1704-1708.	1.0	23
143	Band gap tunability of Type II Antimonide-based superlattices. Physics Procedia, 2010, 3, 1207-1212.	1.2	31
144	Quantum cascade lasers that emit more light than heat. Nature Photonics, 2010, 4, 99-102.	15.6	131

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145	Highly temperature insensitive quantum cascade lasers. Applied Physics Letters, 2010, 97, .	1.5	85
146	On the interface properties of ZnO/Si electroluminescent diodes. Journal of Applied Physics, 2010, 107, 033719.	1.1	14
147	GaN avalanche photodiodes grown on m-plane freestanding GaN substrate. Applied Physics Letters, 2010, 96, .	1.5	36
148	Watt level performance of quantum cascade lasers in room temperature continuous wave operation at Î»â¼3.76â€‚Î¼m. Applied Physics Letters, 2010, 97, .	1.5	59
149	Demonstration of negative differential resistance in GaN/AlN resonant tunneling diodes at room temperature. Journal of Applied Physics, 2010, 107, .	1.1	34
150	Room temperature negative differential resistance characteristics of polar III-nitride resonant tunneling diodes. Applied Physics Letters, 2010, 97, .	1.5	46
151	AlN/GaN double-barrier resonant tunneling diodes grown by metal-organic chemical vapor deposition. Applied Physics Letters, 2010, 96, .	1.5	84
152	Broad area photonic crystal distributed feedback quantum cascade lasers emitting 34 W at Î»â¼4.36â€‚Î¼m. Applied Physics Letters, 2010, 97, .	1.5	45
153	Geiger-mode operation of ultraviolet avalanche photodiodes grown on sapphire and free-standing GaN substrates. Applied Physics Letters, 2010, 96, .	1.5	49
154	Reliability in room-temperature negative differential resistance characteristics of low-aluminum content AlGaN/GaN double-barrier resonant tunneling diodes. Applied Physics Letters, 2010, 97, .	1.5	70
155	III-Nitride Optoelectronic Devices: From ultraviolet detectors and visible emitters towards terahertz intersubband devices. , 2010, , .		1
156	Tunability of intersubband absorption from 4.5 to 5.3â€‚Î¼m in a GaN/Al0.2Ga0.8N superlattices grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2009, 95, 131109.	1.5	20
157	Demonstration of midinfrared type-II InAs/GaSb superlattice photodiodes grown on GaAs substrate. Applied Physics Letters, 2009, 94, .	1.5	55
158	Minority electron unipolar photodetectors based on type II InAs/GaSb/AlSb superlattices for very long wavelength infrared detection. Applied Physics Letters, 2009, 95, .	1.5	85
159	Fabrication and characterization of novel hybrid green light emitting diodes based on substituting n-type ZnO for n-type GaN in an inverted p-n junction. Journal of Vacuum Science & Technology B, 2009, 27, 1784.	1.3	11
160	High-Performance InP-Based Mid-IR Quantum Cascade Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 941-951.	1.9	135
161	Stranskiâ€“Krastanov growth of InGaN quantum dots emitting inÂgreenÂspectra. Applied Physics A: Materials Science and Processing, 2009, 96, 403-408.	1.1	34
162	Comprehensive study of blue and green multi-quantum-well light-emitting diodes grown onÂconventional andÂlateral epitaxial overgrowthÂGaN. Applied Physics B: Lasers and Optics, 2009, 95, 307-314.	1.1	16

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163	Thermal analysis of buried heterostructure quantum cascade lasers for longâ€wavelength infrared emission using 2D anisotropic heatâ€dissipation model. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 356-362.	0.8	12
164	Surface leakage reduction in narrow band gap type-II antimonide-based superlattice photodiodes. Applied Physics Letters, 2009, 94, 053506.	1.5	55
165	Pulsed metal-organic chemical vapor deposition of high-quality AlN/GaN superlattices for near-infrared intersubband transitions. Applied Physics Letters, 2009, 94, 121902.	1.5	27
166	Recent performance records for mid-IR quantum cascade lasers. , 2009, , .		0
167	Background Limited Performance of Long Wavelength Infrared Focal Plane Arrays Fabricated From M-Structure InAsâ€“GaSb Superlattices. IEEE Journal of Quantum Electronics, 2009, 45, 157-162.	1.0	64
168	Quantum dot in a well infrared photodetectors for high operating temperature focal plane arrays. , 2009, , .		2
169	High-performance, continuous-wave quantum-cascade lasers operating up to 85Â°C at Î»â^¼8.8ÂÎ¼m. Applied Physics A: Materials Science and Processing, 2008, 93, 405-408.	1.1	20
170	Investigations of ZnO thin films grown on câ€Al₂O₃ by pulsed laser deposition in N₂ + O₂ ambient. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3084-3087.	0.8	14
171	InP-Based Quantum-Dot Infrared Photodetectors With High Quantum Efficiency and High-Temperature Imaging. IEEE Sensors Journal, 2008, 8, 936-941.	2.4	9
172	Background limited long wavelength infrared type-II InAs/GaSb superlattice photodiodes operating at 110 K. Applied Physics Letters, 2008, 93, 123502.	1.5	87
173	High-Performance Focal Plane Array Based on InAsâ€“GaSb Superlattices With a 10-$mu{hbox {m}}$ Cutoff Wavelength. IEEE Journal of Quantum Electronics, 2008, 44, 462-467.	1.0	29
174	High-Performance Continuous-Wave Operation of $lambda sim {hbox {4.6}}~mu{hbox {m}}$ Quantum-Cascade Lasers Above Room Temperature. IEEE Journal of Quantum Electronics, 2008, 44, 747-754.	1.0	34
175	Electrically Pumped Photonic Crystal Distributed Feedback Quantum Cascade Lasers. Materials Research Society Symposia Proceedings, 2008, 1076, 1.	0.1	0
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